

L Number	Hits	Search Text	DB	Time stamp
1	108981	buried	USPAT; US-PGPUB; JPO	2004/09/19 16:13
2	5541	p-well\$1 same n-well\$1	USPAT; US-PGPUB; JPO	2004/09/19 16:14
3	21222	well\$1 with (conductivity)	USPAT; US-PGPUB; JPO	2004/09/19 16:15
4	155371	(potential or voltage\$1) near2 differen\$3	USPAT; US-PGPUB; JPO	2004/09/19 16:16
5	1122235	semiconduct\$3 or silicon	USPAT; US-PGPUB; JPO	2004/09/19 16:17
6	164757	implant\$3	USPAT; US-PGPUB; JPO	2004/09/19 16:17
7	4006	buried and ((p-well\$1 same n-well\$1) or (well\$1 with (conductivity))) and (semiconduct\$3 or silicon)	USPAT; US-PGPUB; JPO	2004/09/19 16:17
8	576	(buried and ((p-well\$1 same n-well\$1) or (well\$1 with (conductivity))) and (semiconduct\$3 or silicon)) and implant\$3 and ((potential or voltage\$1) near2 differen\$3)	USPAT; US-PGPUB; JPO	2004/09/19 16:18
9	4319	third adj2 well\$1	USPAT; US-PGPUB; JPO	2004/09/19 16:19
10	5	((buried and ((p-well\$1 same n-well\$1) or (well\$1 with (conductivity))) and (semiconduct\$3 or silicon)) and implant\$3 and ((potential or voltage\$1) near2 differen\$3)) not "10"	USPAT; US-PGPUB; JPO	2004/09/19 16:20
11	42	((buried and ((p-well\$1 same n-well\$1) or (well\$1 with (conductivity))) and (semiconduct\$3 or silicon)) and implant\$3 and ((potential or voltage\$1) near2 differen\$3)) and (third adj2 well\$1)	USPAT; US-PGPUB; JPO	2004/09/19 16:24
12	534	((buried and ((p-well\$1 same n-well\$1) or (well\$1 with (conductivity))) and (semiconduct\$3 or silicon)) and implant\$3 and ((potential or voltage\$1) near2 differen\$3)) not (((buried and ((p-well\$1 same n-well\$1) or (well\$1 with (conductivity))) and (semiconduct\$3 or silicon)) and implant\$3 and ((potential or voltage\$1) near2 differen\$3)) and (third adj2 well\$1))	USPAT; US-PGPUB; JPO	2004/09/19 16:24